

Remarkable change of tunneling conductance in YBCO films in fields up to 32.4T

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(Dated: March 22, 2022)

We studied the tunneling density of states in YBCO films under strong currents flowing along node directions. The currents were induced by fields of up to 32.4T parallel to the film surface and perpendicular to the CuO_2 planes. We observed a remarkable change in the tunneling conductance at high fields where the gap-like feature shifts discontinuously from 15meV to a lower bias of 11meV, becoming more pronounced as the field increases. The effect takes place in increasing fields around 9T and the transition back to the initial state occurs around 5T in decreasing fields.

PACS numbers: 74.50.+r, 74.25.Ha

I. INTRODUCTION

The order parameter of a d -wave superconductor has node-lines located at angles $\theta_{\pm} = \pm\pi/4$, where θ is the angle between the quasiparticle momentum and the crystallographic $[1,0,0]$ direction¹. As a result, the tunneling density of states of a d -wave superconductor is significantly different from that of a conventional s -wave superconductor. In particular, it reveals the existence of low energy surface bound states, which are the origin of the zero bias conductance peak at pair breaking surfaces^{2,3}. The high conductance at low bias, below the d -wave gap, is in sharp contrast with the low conductance in an s -wave superconductor at similar bias. The d -wave gap itself is marked in the tunneling density of states by a weak structure called the gap-like feature³ (see Fig. 1). The zero bias conductance peak and gap-like feature are well identified in the tunneling density of states of high- T_c cuprates^{4,5} and simultaneously observed when the surface roughness scale is smaller than the junction size^{5,6}. It was predicted that a d -wave symmetry can be modified by a perturbation that creates a gradient of the order parameter. This is the case of a vortex core⁷, sample surface⁸, and currents^{9,10}.

In this study we report measurements of the conductivity of In/YBCO junctions. Currents in the YBCO film are induced by applying magnetic fields, parallel to the surface and perpendicular to the CuO_2 planes. Films having (110) and (100) orientation are used respectively to induce nodal and anti-nodal currents.

For the (110) orientation the tunneling conductance changes remarkably in high magnetic fields - high currents in a domain that has not been investigated until now, with applied fields reaching up to 32.4T. The position of the gap-like feature shifts down discontinuously in increasing fields around 9T and in decreasing fields around 5T. We argue that these shifts are due to nodal surface currents induced by the applied field, with the field itself, possibly inducing a certain modification of the vortex state. No transition is observed when the field is parallel to the CuO_2 planes (Fig. 1b) or when the film

has the (100) orientation (Fig. 1c). In both cases there are no currents flowing along the nodal direction.

II. EXPERIMENTAL RESULTS

Our oriented films were sputtered onto (110) $SrTiO_3$ and (100) $LaSrGaO_4$. All films have a critical temperature of 89K (slightly underdoped). Tunneling junctions were prepared by pressing a freshly cut Indium pad onto the films' surface¹². These junctions are of high quality, as shown by their low zero bias conductances below the critical temperature of the Indium electrodes¹². A schematic drawing of the crystallographic orientation and experimental setup is shown in Fig. 2.

Tunneling characteristics in (110) films at zero magnetic field exhibit the known zero bias conductance peak and gap-like feature (Fig. 1a). The magnetic field splitting of the zero bias conductance peak was previously addressed^{4,5,6,12,13,14}. We focus here on the field dependence of the gap-like feature at high bias. It shows a progressive, roughly linear, shift of the peak position from 17 meV to 15 meV as the field increases from 0 to 1T. This initial decrease is followed by a flat region up to 6T. If that field is not exceeded and then reversed a hysteresis loop is described ending up with a flat region at low field. If the field is increased above 6T the gap-like feature amplitude starts to shrink until, at 8T, it can't be identified anymore. In the range of 8 to 11T a flat maximum develops between 10 and 15 meV. An 11 meV peak builds up with the field and is clearly identified above 11T. Up to a field of 16T, no detectable smearing of this peak occurs.

Reducing the field from values larger than 11T has another interesting effect. The 11 meV peak gradually shifts back to 14 meV as the field is reduced by about 1T, for example from 15 to 14T (Fig. 3) or from 32.4 to 31.5T (Fig. 4b). In contrast to the 9T field up transition, the shift back to 14 meV is *continuous*, which shows that the new peak at 11 meV is indeed a new gap like feature rather than being related for instance to the split zero-bias conductance peak. By further reducing the field, the

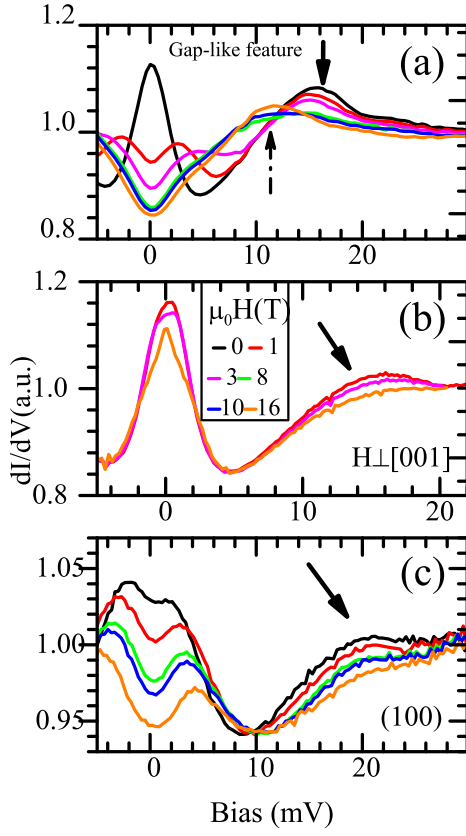


FIG. 1: dI/dV versus bias voltage; magnetic field applied parallel to the films surface up to 16T at 4.2K. (a) A (110) in-plane orientated film at increasing field. The field is perpendicular to the CuO_2 planes (sample 1). (b) A (110) in-plane orientated film at increasing field. The field is parallel to the CuO_2 planes (sample 1). (c) A (100) in-plane orientated film. The field is perpendicular to the CuO_2 planes. Solid (dashed) arrows indicate the gap like feature positions at low (high) fields. Note that only when the field is perpendicular to the CuO_2 planes and the normal to the film surface is a nodal direction, a remarkable change in the spectrum is observed at high fields.

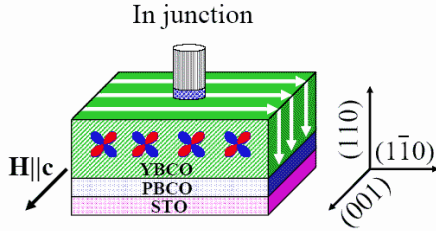


FIG. 2: Schematic presentation of the measurement setup for the (110) films. Indium pads are pressed against the surface of the oriented thin film. The orientation of the film enables us to apply a magnetic field parallel or perpendicular to the CuO_2 layers while the field is kept parallel to the films' surface and perpendicular to the tunneling current.

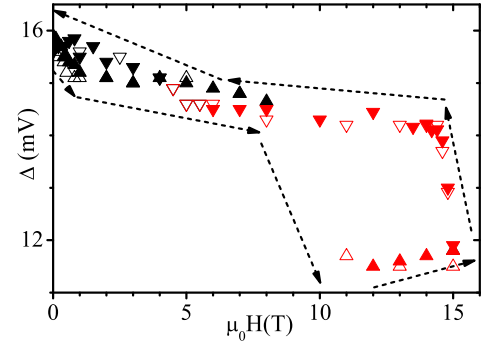


FIG. 3: Gap-like feature position for sample 1 in increasing (Δ) and decreasing (∇) magnetic fields at 4.2K. Data taken both for positive (full) and negative (hollow) field polarity. Black (red) represent the low (high) field state

14 meV peak shrinks while the 16 meV builds up below 5T (Fig. 5a). An analogous behavior is seen under field cooled conditions (Fig. 5b).

The overall variation of the gap-like feature peak position with respect to the applied field can be seen in Fig. 3. The jump in its position can be clearly observed in increasing fields above 8T and decreasing fields lower than 6T. The gradual increase of the 11meV peak amplitude as the field is increased beyond 10T (Fig. 6) suggests that it characterizes a new superconducting state.

III. DISCUSSION

The rapid change in the peak position upon field reversal (Figs. 3, 4b) means that its position is affected by field induced currents. The strong difference between (100) and (110) oriented films, both showing a similar gap-like feature, presumably due to surface roughness⁶, indicates that these currents flow over a depth much larger than the surface roughness (few tens of nm).

The Bean-Livingston barrier¹⁵ can prevent the entry of vortices up to fields of the order of the thermodynamical critical field, H_c (~ 1 T for YBCO). The rapid initial decrease of the gap-like feature peak position from 16 meV down to 14 meV over that field range can be due to the delayed vortex entrance (see Fig. 3). We name the corresponding currents surface vortex currents, j_V . This is confirmed by the low field hysteresis loop, as there is no Bean-Livingston barrier in decreasing fields. This initial decrease is not observed in (100) oriented films where the currents at the surface flow along an anti-nodal direction. This decrease is therefore clearly due to nodal currents. The major question raised here concerns however the origin of the 11 meV peak seen in increasing fields above 10T. It could be a current effect, or a field effect, or a combination of both.

In addition to the vortex surface currents, j_V , one should also consider The Meissner screening current, j_M , and the Bean current j_B due to vortices pinned in the

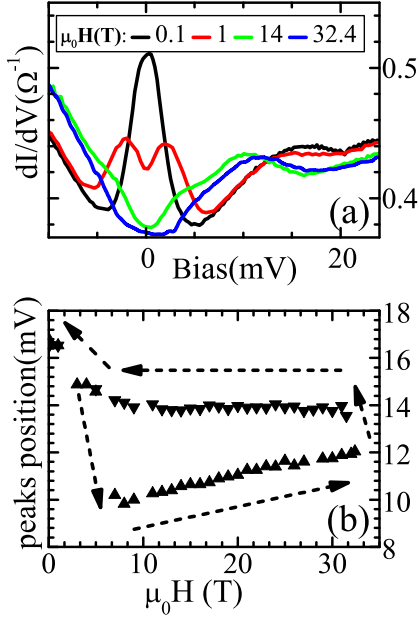


FIG. 4: (a) dI/dV versus bias voltage for sample 2 measured at 1.3K in increasing magnetic fields. (b) gap-like feature position in increasing (Δ) and decreasing (∇) fields.

bulk. We showed¹⁴ that by measuring the difference between field cooled and decreasing field splitting values of the zero bias conductance peak (also due to the surface currents⁶), one can estimate the Bean critical current value. We found that j_B is roughly constant up to fields of 16T and has a value of a few tens of MA/cm².

The surface current can be obtained by calculating the depth, d , of the vortex-core free area at the sample surface¹⁵. Its derivation is not affected by the d -wave symmetry and has to include the Bean current j_B . In the following the effect of the vortex surface current is neglected. Consider a semi-infinite superconductor in a uniform magnetic field H . The field inside, $b(x)$, is the solution of London's equation which has to match the boundary conditions $b(0) = H$, $b(d) = \tilde{B}$ and the vortex matter equilibrium condition $j(d) = j_B$, where \tilde{B} is the local induction value. In the field range $H_{c1} \ll H \ll H_{c2}$ we have $d \ll \lambda$ and $j_B \ll j_M$:

$$d \approx \lambda \sqrt{2(H - \tilde{B})/H + 4\pi j_B \lambda^2 / cH}, \quad (1)$$

where λ is London's penetration depth. The same approximation results in $\tilde{B} \approx B$, where B is the equilibrium induction, $j \approx j_M(H) + j_B$ in increasing fields and $j \approx j_M(H) - j_B$ in decreasing fields, where:

$$j_M = \frac{c}{4\pi\lambda} \sqrt{-8\pi H M} = \frac{c}{4\pi\lambda^2} \sqrt{\frac{\phi_0 H}{4\pi} \ln \frac{H_{c2}}{H}}, \quad (2)$$

and ϕ_0 is the flux quantum. We find $j_M \sim 2.2 \cdot 10^8$ A/cm² for $H = 90$ KOe, $\lambda = 1500 \text{ \AA}$ and $H_{c2} = 1,200$ KOe.

We emphasize that the contributions of j_V , j_M and j_B may all be important for the interpretation of the

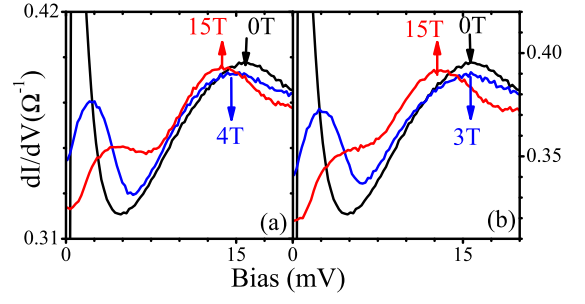


FIG. 5: dI/dV versus bias voltage for sample 3 measured at 0.5K. (a) Decreasing fields from 16T. (b) Field cooled conditions. Note that the intermediate field peak conductance is lower than both the high and low field ones.

experiment. The field reversal effect can be explained by j_B and/or j_V . After field reversal, j_B changes sign while j_V is negligible¹⁵.

We note that the progressive enhancement of the 11meV peak in increasing fields (Fig. 6) suggests a transition to a new superconducting state. Any continuous reduction of the d -wave gap would not be accompanied by an enhancement of its gap-like feature peak amplitude.

The new superconducting phase could be a different vortex state¹⁷, in such case the transition would be basically field induced. Alternatively, the new phase could appear due to strong nodal currents and possibly have an order parameter with a symmetry different from a pure d -wave^{9,10}.

A general difficulty in comparing our data to existing theories is that they have addressed only the small current limit^{9,10,11}. We can only offer some speculations as to what a high current phase might be. In a previous publication¹³ we discussed the zero bias conductance peak splitting in terms of a field-induced id_{xy} component. But we have found no correlation between the zero bias conduction peak splitting and the gap like feature position implying that their origins are different. For instance, after decreasing the field from 16 to 15T, the position of the gap-like feature remains unchanged down to 5T (see Fig. 3), but the zero-bias conductance peak splitting reduce from 4.2 to 2.5 meV (see Fig.4 in Ref.¹³). We speculate that surface currents on the coherence length scale could split the zero bias peak,⁶ but, as shown here, only currents on much larger length scale are affecting the position of the gap like feature position.

The fact that we observe a regime where two gap features coexist, both in increasing and decreasing fields as well as in field cooled conditions, with a definite hysteresis, suggests a first order transition showing superheating and supercooling effects. To be specific, following the position and amplitude of the gap-like feature as a function of applied field we observed that the transition from low to high fields state takes place at 9T (superheating) and back from the high to low fields at 5T (supercooling).

Whatever the high current - high field phase is, it is

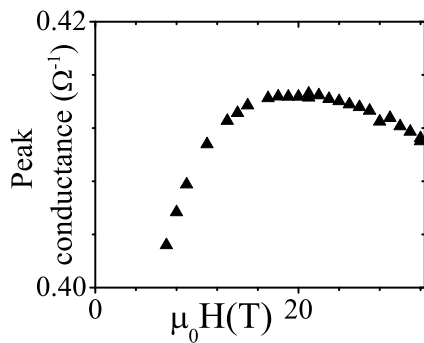


FIG. 6: 11 meV gap-like feature peak amplitude of sample 2 for increasing fields. The enhancement up to 20T suggests that the high fields state has a stronger coherence peak.

clear that it has the effect of reducing the density of low lying states, and this well beyond the field-current where the zero bias conductance peak has disappeared (Fig. 4a). A transition to an inhomogeneous state in the case of nodal currents was recently speculated about by Khavkine *et. al.*⁹. We also note that in very high fields the vortices nearest to the surface are located within a few coherence lengths, which may affect the tunneling conductance¹⁶.

A different explanation to the data would be that the remarkable change in the tunneling conductance at 9T in increasing fields is a vortex state transition e.g. Bragg to vortex glass¹⁸. Such a transition is known to be irreversible as observed. The new vortex state could modify the pinning and hence the total nodal current or its' effect on the order parameter. This could explain the large hysteresis observed at high fields. However, in contradiction to the high bias region, the low bias region which is also sensitive to total current via the Doppler shift

mechanism,⁶ does not show substantial hysteresis.

IV. SUMMARY

In conclusion, we have observed a remarkable change in the tunneling conductance in high magnetic fields in YBCO (110) oriented films. A transition of the gap-like feature position and amplitude is present in both increasing and decreasing fields and under field cooled conditions for fields oriented parallel to the surface and perpendicular to the CuO_2 planes in such a way as to induce currents along nodal directions. We have proposed that the observed transition may be induced by these currents. In the high current state, the density of low energy states is reduced, possibly indicating the emergence of a component of the order parameter leading towards a fully gaped state. Alternatively, the changes in the tunneling characteristics may be due to a transition between two vortex states, having different gap values and sensitivity to nodal currents.

This work was supported by the Heinrich Herz-Minerva Center for High Temperature Superconductivity, the Israel Science Foundation, the Oren Family Chair of Experimental Solid State Physics and NSF grant DMR 01-02350. Work carried out at the National High Magnetic Field Laboratory at Tallahassee is supported by an NSF cooperative agreement DMR-00-84173 and the State of Florida. The work of R.M. was supported in part by grant No. 2000011 from the United States – Israel Binational Science Foundation (BSF), Jerusalem, Israel. G.D. is indebted to Philippe Nozieres for very helpful discussions. We are indebted to Amlan Biswas (UF) for his contribution to the NHMFL experiment and to Amir Kohen for discussions.

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